



#17/Supp  
Amend C  
4.3.03 Moore  
Docket No.: M4065.0475/P475  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
John Moore

Application No.: 09/938,672

Group Art Unit: 2152

Filed: August 27, 2001

Examiner: T. Washington

For: METHOD OF FABRICATING DUAL  
PCRAM CELLS SHARING A COMMON  
ELECTRODE (as amended)

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SUPPLEMENTAL AMENDMENT

Commissioner For Patents  
Washington, D.C. 20231  
Dear Sir:

Further to the Amendment of January 24, 2003, please further amend the  
above-identified U.S. application as follows:

IN THE CLAIMS:

Please amend the claims as follows.

C<sup>1</sup>  
17. (Twice Amended) A method of fabricating a memory device comprising:  
forming a first memory cell to include a chalcogenide glass material having a  
changeable resistance and cathode and anode electrodes spaced apart and in contact with  
said chalcogenide glass material;

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